

CMWSH-4

SURFACE MOUNT  
SCHOTTKY DIODE

**SUPER**mini™



SOT-343 CASE

**Central**™  
**Semiconductor Corp.**

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMWSH-4, 40V, Low  $V_F$ , Dual, Galvanically isolated Silicon Schottky diode, is designed for use in high speed surface mount switching applications.

**Marking Code is WSH4.**

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

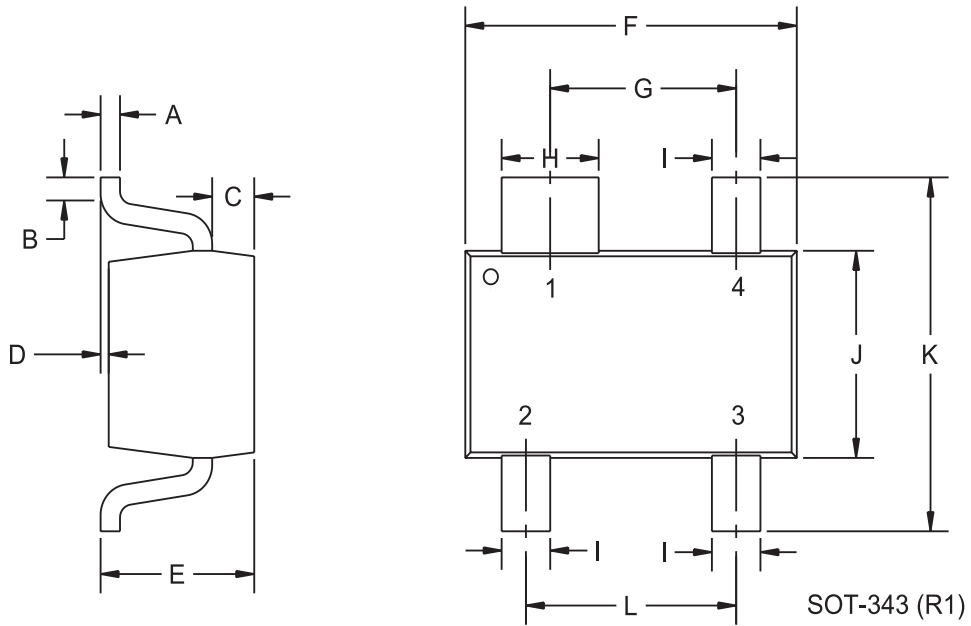
	<b>SYMBOL</b>		<b>UNITS</b>
Peak Repetitive Reverse Voltage	$V_{RRM}$	40	V
Continuous Forward Current	$I_F$	100	mA
Peak Repetitive Forward Current	$I_{FRM}$	350	mA
Forward Surge Current, $t_p=10$ ms	$I_{FSM}$	750	mA
Power Dissipation	$P_D$	350	mW
Operating and Storage Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
Thermal Resistance	$\theta_{JA}$	357	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS PER DIODE:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

<b>SYMBOL</b>	<b>TEST CONDITIONS</b>	<b>MIN</b>	<b>TYP</b>	<b>MAX</b>	<b>UNITS</b>
$I_R$	$V_R=25\text{V}$		90	500	nA
$I_R$	$V_R=25\text{V}, T_A=100^\circ\text{C}$		25	100	$\mu\text{A}$
$I_R$	$V_R=40\text{V}$		0.23	5.0	$\mu\text{A}$
$V_F$	$I_F=2.0\text{mA}$		0.29	0.33	V
$V_F$	$I_F=15\text{mA}$		0.40	0.45	V
$V_F$	$I_F=100\text{mA}$		0.52	0.60	V
$C_T$	$V_R=1.0\text{V}, f=1.0\text{MHz}$		10.0		pF
$t_{rr}$	$I_F=I_R=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$			5.0	ns

R0 ( 27-August 2001)

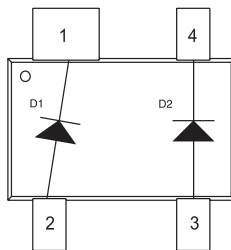
**SOT-343 CASE - MECHANICAL OUTLINE**



SOT-343 (R1)

**LEAD CODE:**

- 1) CATHODE D1
- 2) ANODE D1
- 3) ANODE D2
- 4) CATHODE D2



**MARKING CODE: WSH4**

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.005		0.12	
B	0.006		0.15	
C	0.010	0.011	0.26	0.29
D	0.001	0.003	0.03	0.07
E	0.034	0.037	0.87	0.93
F	0.081		2.05	
G	0.045		1.15	
H	0.022	0.025	0.57	0.63
I	0.011	0.013	0.27	0.33
J	0.047	0.049	1.20	1.25
K	0.079	0.085	2.00	2.15
L	0.051		1.30	

SOT-343 (REV: R1)